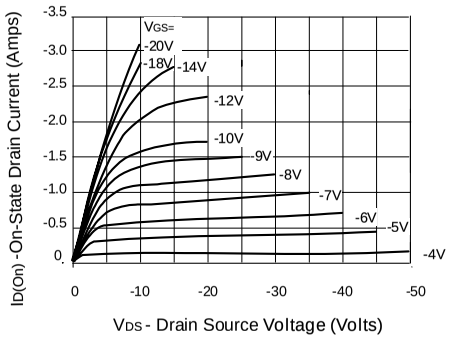
THE DATASHEET OF

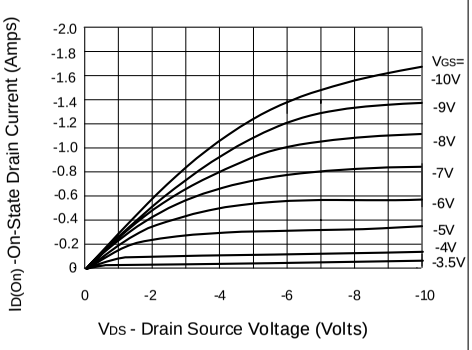
ZVP2106ASTZ

ZVP2106A

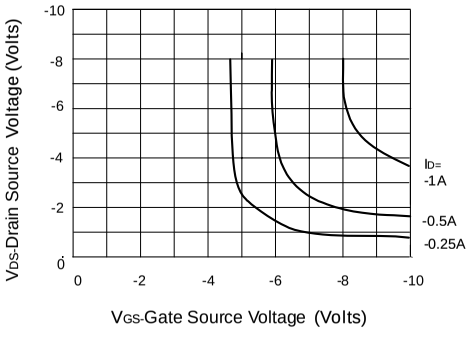
TYPICAL CHARACTERISTICS



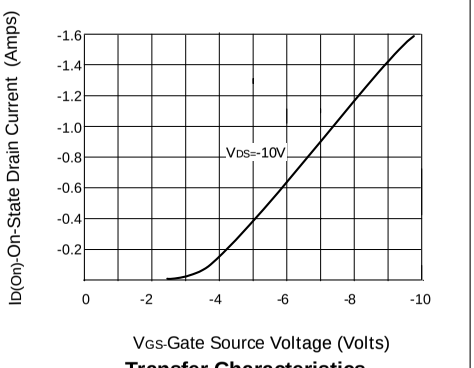
Output Characteristics



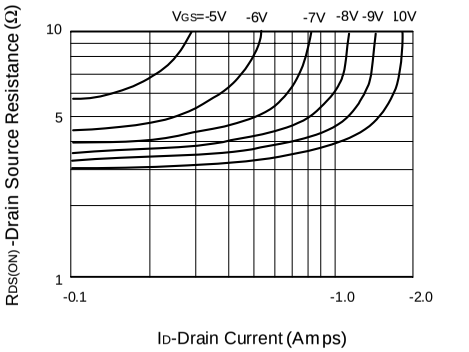
Saturation Characteristics



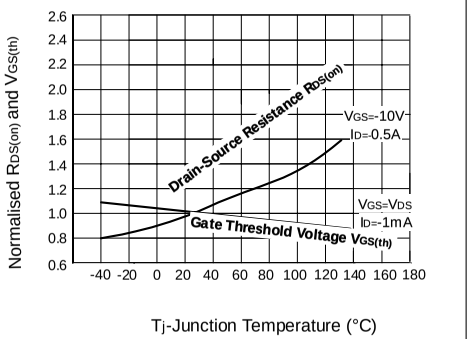
Voltage Saturation Characteristics



Transfer Characteristics



On-resistance v drain current



Normalised $R_{DS(on)}$ and $V_{GS(th)}$ vs Temperature

P-CHANNEL ENHANCEME
MODE VERTICAL DMOS F

ISSUE 2 – MARCH 94

FEATURES

* 60 Volt V_{DS}
* $R_{DS(on)}$=5Ω

ABSOLUTE MAXIMUM RATINGS

PARAMETER
Drain-Source Voltage
Continuous Drain Current at T_{amb}=25°C
Pulsed Drain Current
Gate Source Voltage
Power Dissipation at T_{amb}=25°C
Operating and Storage Temperature R

ELECTRICAL CHARACTERISTICS

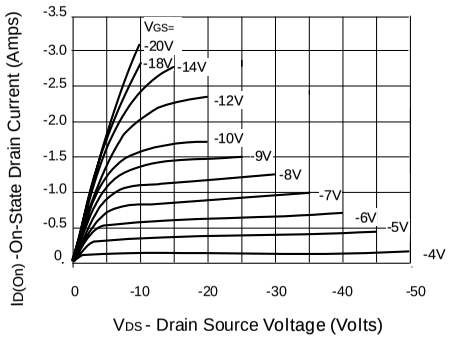
PARAMETER	SYMBO
Drain-Source Breakdown Voltage	BV_{DSS}
Gate-Source Threshold Voltage	$V_{GS(th)}$
Gate-Body Leakage	I_{GSS}
Zero Gate Voltage Drain Current	I_{DSS}
On-State Drain Current(1)	$I_{D(on)}$
Static Drain-Source On-State Resistance (1)	$R_{DS(on)}$
Forward Transconductance (1)(2)	g_{fs}
Input Capacitance (2)	C_{iss}
Common Source Output Capacitance (2)	C_{oss}
Reverse Transfer Capacitance (2)	C_{rss}
Turn-On Delay Time (2)(3)	$t_{d(on)}$
Rise Time (2)(3)	t_r
Turn-Off Delay Time (2)(3)	$t_{d(off)}$
Fall Time (2)(3)	t_f

(1) Measured under pulsed conditions. Wid
(2) Sample test.

Switching times measured with 50Ω sourc

ZVP2106A

TYPICAL CHARACTERISTICS



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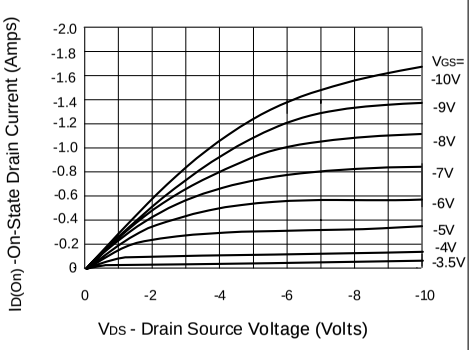

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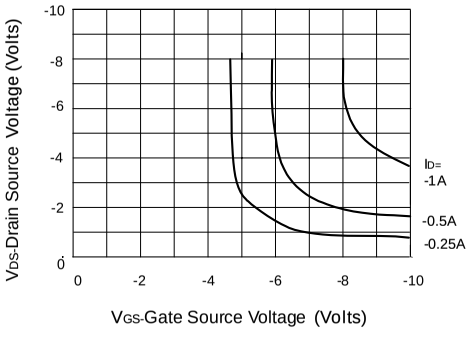

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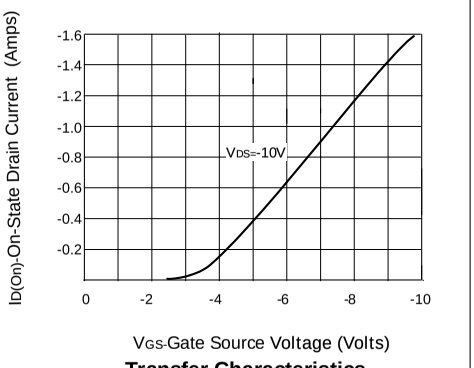

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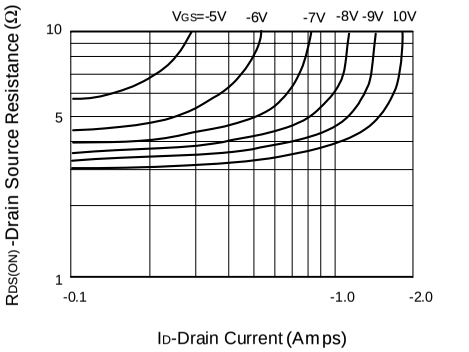

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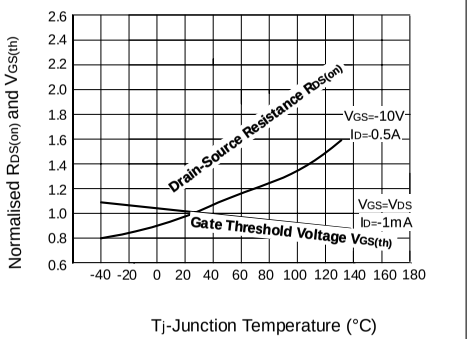

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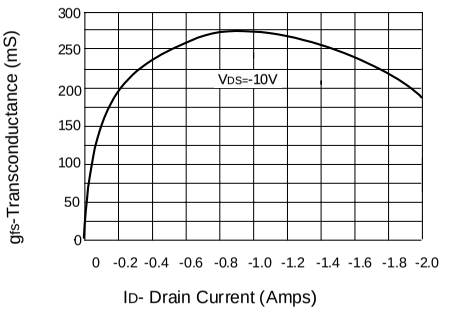
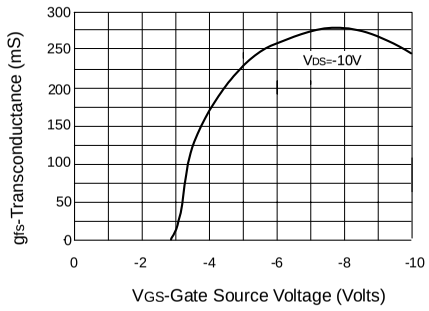
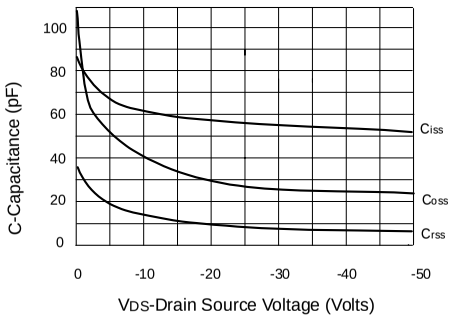


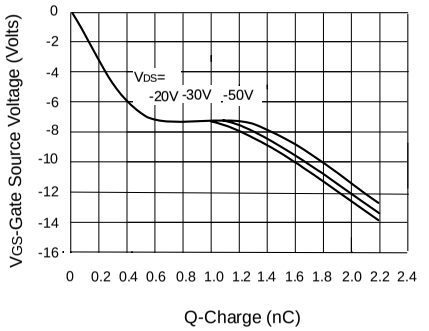
Transconductance v drain current



Transconductance v gate-source voltage



Capacitance v drain-source voltage



Gate charge v gate-source voltage

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